Vishay Semiconductors

# 650 V Gen 4 Power Silicon Carbide Schottky Diode, 6 A



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## LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS								
I <sub>F</sub> 6 A								
V <sub>R</sub>	650 V							
V <sub>F</sub> at I <sub>F</sub> at 25 °C, typ.	1.3 V							
T <sub>J</sub> max.	175 °C							
I <sub>R</sub> at V <sub>R</sub> at 175 °C	35 µA typ.							
Q <sub>C</sub> (V <sub>R</sub> = 400 V)	16 nC							
Package	TO-220AC 2L							
Circuit configuration	Single							

## FEATURES

Positive V<sub>F</sub> temperature coefficient for easy paralleling



COMPLIANT HALOGEN

FREE

- Virtually no recovery tail and no switching losses
- Temperature invariant switching behavior
- 175 °C maximum operating junction temperature
- Meets JESD 201 class 1 A whisker test
- Solder bath temperature 275 °C maximum, 10 s per JESD 22-B106
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

## **DESCRIPTION / APPLICATIONS**

Wide band gap SiC based 650 V Schottky diode, designed for high performance and ruggedness.

Optimized for extreme high speed hard switching across a wide temperature range. This SiC diode is ideal for demanding applications such as high efficiency PFC diodes and ultra high frequency output rectifiers in AC/DC and DC/DC converters.

### **MECHANICAL DATA**

Case: TO-220AC 2L

Molding compound meets UL 94 V-0 flammability rating Base P/N-M3 - halogen-free, RoHS-compliant

**Terminals:** matte tin plated leads, solderable per J-STD-002 and JESD 22-B102

Mounting torque: 10 in-lbs maximum

MAXIMUM RATINGS (T <sub>A</sub> = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Peak repetitive reverse voltage	V <sub>RRM</sub>		650	V					
Continuous forward current	I <sub>F</sub> <sup>(1)</sup>	T <sub>C</sub> = 152 °C (DC)	6	А					
Continuous forward current	I <sub>F</sub> <sup>(2)</sup>	T <sub>C</sub> = 145 °C (DC)	6	А					
DC blocking voltage	V <sub>DC</sub>		650	V					
Repetitive peak forward current	I <sub>FRM</sub>	$T_C = 25$ °C, f = 50 Hz, square wave, DC = 25 %	28	А					
Non repetitive peak forward owner ownert	1	$T_{C}$ = 25 °C, $t_{p}$ = 10 ms, half sine wave	39	٨					
Non-repetitive peak forward surge current	I <sub>FSM</sub>	$T_C = 110 \text{ °C}, t_p = 10 \text{ ms}, \text{ half sine wave}$	36	A					
	P <sub>tot</sub> <sup>(1)</sup>	$T_{C} = 25 \ ^{\circ}C$	59	w					
Power dissipation		T <sub>C</sub> = 110 °C	25.5						
Power dissipation	P <sub>tot</sub> <sup>(2)</sup>	T <sub>C</sub> = 25 °C	45	vv					
	Ptot (=)	T <sub>C</sub> = 110 °C	19.5						
l <sup>2</sup> t value	¢.2	T <sub>C</sub> = 25 °C	7.6	A <sup>2</sup> s					
I-L VAIUE	∫i <sup>2</sup> dt	T <sub>C</sub> = 110 °C	6.5	A-S					
Operating junction and storage temperatures	T <sub>J</sub> <sup>(3)</sup> , T <sub>Stg</sub>		-55 to +175	°C					

#### Notes

<sup>(1)</sup> Based on typical R<sub>th</sub>

<sup>(2)</sup> Based on maximum R<sub>th</sub>

<sup>(3)</sup> The heat generated must be less than the thermal conductivity from junction-to-ambient:  $dP_D/dT_J < 1/R_{\theta JA}$ 

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## **Vishay Semiconductors**

<b>ELECTRICAL SPECIFICATIONS</b> ( $T_J$ = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
		I <sub>F</sub> = 6 A	-	1.3	1.5				
Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 6 A, T <sub>J</sub> = 150 °C	-	1.45	1.75	V			
		I <sub>F</sub> = 6 A, T <sub>J</sub> = 175 °C	-	1.55	-				
	I <sub>R</sub>	V <sub>R</sub> = V <sub>R</sub> rated	-	1.5	60	μA			
Reverse leakage current		$V_R = V_R$ rated, $T_J = 150$ °C	-	17	120				
		$V_R = V_R$ rated, $T_J = 175 \text{ °C}$	-	35	-				
Total capacitance	С	V <sub>R</sub> = 1 V, f = 1 MHz	-	266	-	- 5			
		V <sub>R</sub> = 400 V, f = 1 MHz	-	24	-	pF			
Total capacitive charge	Q <sub>C</sub>	V <sub>R</sub> = 400 V, f = 1 MHz	-	16	-	nC			

THERMAL AND MECHANICAL SPECIFICATIONS (T <sub>A</sub> = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL TEST CONDITIONS MIN. TYP. MAX. UNITS								
Thermal resistance, junction-to-case	R <sub>thJC</sub>		-	2.5	3.3	°C/W			
Marking device		4C06ET07T							

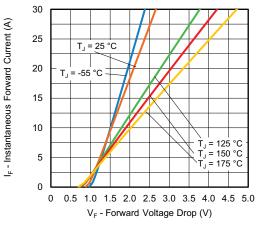


Fig. 1 - Typical Forward Voltage Drop Characteristics

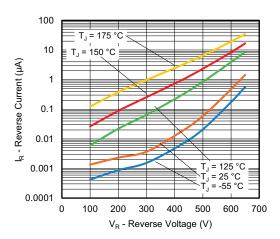


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

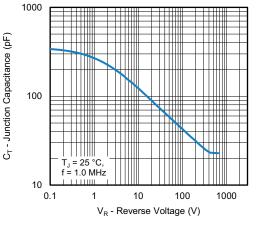


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

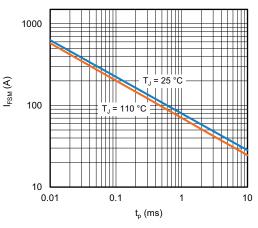
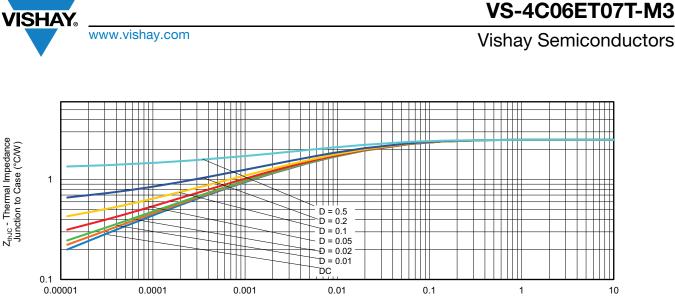


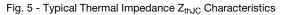
Fig. 4 - Non-Repetitive Peak Forward Surge Current vs. Pulse Duration (Square Wave)

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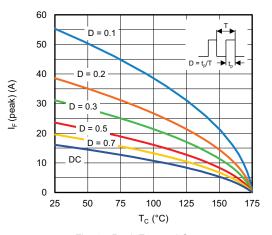


Fig. 6 - Peak Forward Current vs. Maximum Allowable Case Temperature

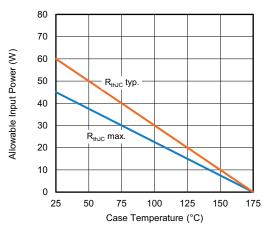


Fig. 7 - Forward Power Loss Characteristics

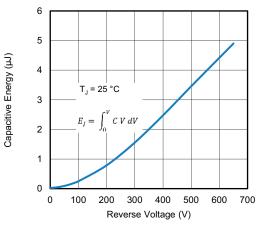


Fig. 8 - Typical Capacitive Energy vs. Reverse Voltage

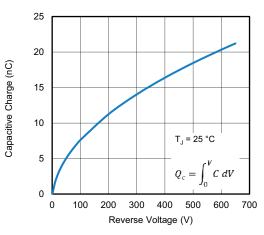


Fig. 9 - Typical Capacitive Charge vs. Reverse Voltage

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lead (Pb)-free

## **ORDERING INFORMATION TABLE**

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Device code	VS-	4C	06	E	т	07	т	-M3			
		2	3	4	5	6	7	8			
	1 - Vishay Semiconductors product										
	<b>2</b> - 4C = SiC diode, Generation 4										
	3 -	· Cur	rent rati	ng (06 =	= 6 A)						
	4 -	E=	single c	diode							
	5 -	- Pac	kage T	D-220							
	6 - Voltage rating: (07 = 650 V)										
	7 -	- T = true 2 pin									
	8 -	- Env	Environmental digit:								
		M3	M3 = halogen-free, RoHS-compliant, and terminatio								

ORDERING INFORMATION										
PREFERRED P/N	UNIT WEIGHT	BASE QUANTITY	PACKAGING DESCRIPTION							
VS-4C06ET07T-M3	2.0 g	50 / tube	Antistatic plastic tubes							

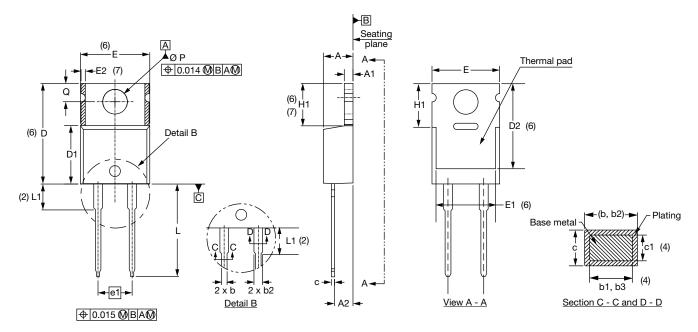
LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?96069
Part marking information	www.vishay.com/doc?95391



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TO-220AC 2L

## **DIMENSIONS** in millimeters and inches



SYMBOL	MILLIMETERS		INC	HES	NOTES	NOTES	SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STNIDUL	MIN.	MAX.	MIN.	MAX.	NOTES		STIVIDUL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.25	4.65	0.167	0.183			E1	6.86	8.89	0.270	0.350	6
A1	1.14	1.40	0.045	0.055			E2	-	0.76	-	0.030	7
A2	2.56	2.92	0.101	0.115			e1	4.88	5.28	0.192	0.208	
b	0.69	1.01	0.027	0.040			H1	5.84	6.86	0.230	0.270	6, 7
b1	0.38	0.97	0.015	0.038	4		L	13.52	14.02	0.532	0.552	
b2	1.20	1.73	0.047	0.068			L1	3.32	3.82	0.131	0.150	2
b3	1.14	1.73	0.045	0.068	4		ØΡ	3.54	3.73	0.139	0.147	
с	0.36	0.61	0.014	0.024			Q	2.60	3.00	0.102	0.118	
c1	0.36	0.56	0.014	0.022	4							
D	14.85	15.25	0.585	0.600	3							
D1	8.38	9.02	0.330	0.355								
D2	11.68	12.88	0.460	0.507	6							
E	10.11	10.51	0.398	0.414	3, 6							

Notes

<sup>(1)</sup> Dimensioning and tolerancing as per ASME Y14.5M-1994

<sup>(2)</sup> Lead dimension and finish uncontrolled in L1

(3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

(4) Dimension b1, b3 and c1 apply to base metal only

<sup>(5)</sup> Controlling dimension: inches

<sup>(6)</sup> Thermal pad contour optional within dimensions E, H1, D2 and E1

<sup>(7)</sup> Dimension E2 x H1 define a zone where stamping and singulation irregularities are allowed

<sup>(8)</sup> Outline conforms to JEDEC<sup>®</sup> TO-220, except D2, where JEDEC<sup>®</sup> minimum is 0.480"

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